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TRANSMITTAL FORM

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Total Number of Pages in This Submission

Application Number	09/517541
Filing Date	2 March 2000
First Named Inventor	Kia Silverbrook
Art Unit	3628
Examiner Name	Nga B Nguyen
Attorney Docket Number	AUTH15US

ENCLOSURES *(Check all that apply)*

- ☐ Fee Transmittal Form
  - ☐ Fee Attached
- ☑ Amendment/Reply
  - ☐ After Final
  - ☐ Affidavits/declaration(s)
- ☐ Extension of Time Request
- ☐ Express Abandonment Request
- ☐ Information Disclosure Statement
- ☐ Certified Copy of Priority Document(s)
- ☐ Reply to Missing Parts/ Incomplete Application
  - ☐ Reply to Missing Parts under 37 CFR 1.52 or 1.53
- ☐ Drawing(s)
- ☐ Licensing-related Papers
- ☐ Petition
- ☐ Petition to Convert to a Provisional Application
- ☐ Power of Attorney, Revocation Change of Correspondence Address
- ☐ Terminal Disclaimer
- ☐ Request for Refund
- ☐ CD, Number of CD(s) _____
  - ☐ Landscape Table on CD
- ☐ After Allowance Communication to TC
- ☐ Appeal Communication to Board of Appeals and Interferences
- ☐ Appeal Communication to TC **(Appeal Notice, Brief, Reply Brief)**
- ☐ Proprietary Information
- ☐ Status Letter
- ☐ Other Enclosure(s) (please Identify below):

Remarks

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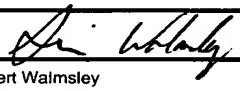
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm Name			
Signature			
Printed name	Kia Silverbrook,Simon Robert Walmsley		
Date	March 23, 2006	Reg. No.	

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In the United States Patent and Trademark Office

Serial Number:	09/517,541		
Application. Filed:	March 02, 2000		
Applicant:	Kia Silverbrook and Simon Robert Walmsley		
Application Title:	Shielding Manipulations of Secret Data		
Examiner/GAU:	NGA B Nguyen		3628
		Dated	March 23, 2006
		At:	Balmain, NSW
		Docket No.	AUTH15US

REPLY

Commissioner for Patents
Washington, District of Columbia 20231

Dear Sir:

In response to the Examiner's further Office Action of February 3, 2006 in the present RCE application the Applicant submits the accompanying text book extracts and the below Remarks.

Regarding Response to Arguments/Amendment

In the Office Action, the Examiner submits that the Applicant has not submitted any rebuttal of the well known statements made by the Examiner in the previous and current Office Actions, but has merely requested references disclosing the well known limitations.

The following is a specific rebuttal of the Examiner's statement of what is purported to be well known in the art.

Typical CMOS circuit applications, in which it is ensured that both nMOS and pMOS transistors do not turn on at the same time, are high current output drivers (at output pads) to minimise the peak current taken from the power supply. Such high current output drivers are not useable to manipulate any type of data, let alone secret data as claimed in the claimed invention.

In designing CMOS circuits for manipulating data it is well known to make the circuits as simple as possible, by using the minimum number of transistors and minimum size transistors consistent with the speed requirements of the circuit. These circuits then allow both nMOS and pMOS transistors to turn on momentarily which risks the emission of a light pulse, making the CMOS structure a "flashing" CMOS structure, as described by the present inventors in the present application.

The accompanying extracted pages of "Principles of CMOS VLSI design" clearly show that it is well known that conventional CMOS logic (which is based on the CMOS inverter) has a region during a change of state where both nMOS and pMOS transistors are turned on, and therefore exhibit intermediate resistance.